

MOS FIELD EFFECT TRANSISTOR $\mu PA2800$

SWITCHING N-CHANNEL POWER MOSFET

DESCRIPTION

The μ PA2800 is N-channel MOSFET designed for DC/DC converter and power management applications of portable equipments.

FEATURES

• Low on-state resistance

 $R_{DS(on)1} = 7.3 \text{ m}\Omega \text{ MAX.} \text{ (VGS = 10 V, ID = 17 A)}$

 $R_{DS(on)2} = 10 \text{ m}\Omega \text{ MAX.} \text{ (V}_{GS} = 4.5 \text{ V}, I_D = 8.5 \text{ A)}$

- Built-in gate protection diode
- Thin type surface mount package with heat spreader
- RoHS Compliant

ABSOLUTE MAXIMUM RATINGS (T_A = 25°C, All terminals are connected.)

Drain to Source Voltage (Vgs = 0 V)	VDSS	30	V
Gate to Source Voltage (VDS = 0 V)	Vgss	±20	V
Drain Current (DC)	ID(DC)	±17	Α
Drain Current (pulse) Note1	I _{D(pulse)}	±102	Α
Total Power Dissipation Note2	P _{T1}	1.5	W
Total Power Dissipation (PW = 10 sec) Note2	P _{T2}	3.8	W
Channel Temperature	Tch	150	°C
Storage Temperature	Tstg	-55 to +150	°C
Single Avalanche Current Note3	las	17	Α
Single Avalanche Energy Note3	Eas	28.9	mJ

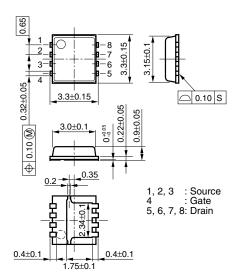
THERMAL RESISTANCE

Channel to Ambient Thermal Resistance $^{\rm Note2}$	Rth(ch-A)	83.3	°C/W
Channel to Case (Drain) Thermal Resistance	Rth(ch-C)	2.4	°C/W

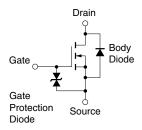
Notes 1. PW \leq 10 μ s, Duty Cycle \leq 1%

- 2. Mounted on FR-4 board of 25.4 mm x 25.4 mm x 0.8 mmt
- 3. Starting T_{ch} = 25°C, V_{DD} = 15 V, R_G = 25 Ω , V_{GS} = 20 \rightarrow 0 V, L = 100 μ H

PACKAGE DRAWING (Unit: mm)



EQUIVALENT CIRCUIT



Remark The diode connected between the gate and source of the transistor serves as a protector against ESD. When this device actually used, an additional protection circuit is externally required if a voltage exceeding the rated voltage may be applied to this device.

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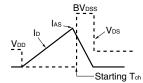
ELECTRICAL CHARACTERISTICS (TA = 25°C, All terminals are connected.)

CHARACTERISTICS	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT
Zero Gate Voltage Drain Current	IDSS	V _{DS} = 30 V, V _{GS} = 0 V			10	μA
Gate Leakage Current	Igss	V _{GS} = ±20 V, V _{DS} = 0 V			±10	μΑ
Gate to Source Cut-off Voltage	V _{GS(off)}	V _{DS} = 10 V, I _D = 1 mA	1.0		2.5	V
Forward Transfer Admittance Note	yfs	V _{DS} = 10 V, I _D = 8.5 A	7			S
Drain to Source On-state Resistance Note	RDS(on)1	V _{GS} = 10 V, I _D = 17 A		6.0	7.3	mΩ
	RDS(on)2	V _{GS} = 4.5 V, I _D = 8.5 A		7.8	10	mΩ
Input Capacitance	Ciss	V _{DS} = 15 V,		1770		pF
Output Capacitance	Coss	V _{GS} = 0 V,		260		pF
Reverse Transfer Capacitance	Crss	f = 1 MHz		150		pF
Turn-on Delay Time	t _{d(on)}	V _{DD} = 15 V, I _D = 8.5 A,		12		ns
Rise Time	tr	V _{GS} = 10 V,		19		ns
Turn-off Delay Time	t _{d(off)}	R _G = 10 Ω		54		ns
Fall Time	t f			13		ns
Total Gate Charge	Q _G	V _{DD} = 15 V,		17		nC
Gate to Source Charge	Qgs	V _{GS} = 5 V,		5.1		nC
Gate to Drain Charge	Q _{GD}	I _D = 17 A		6.7		nC
Body Diode Forward Voltage Note	V _{F(S-D)}	I _F = 17 A, V _{GS} = 0 V		0.83		V
Reverse Recovery Time	trr	I _F = 17 A, V _{GS} = 0 V,		25		ns
Reverse Recovery Charge	Qrr	di/dt = 100 A/μs		18		nC
Gate Resistance	Rg	f = 1 MHz		1.5		Ω

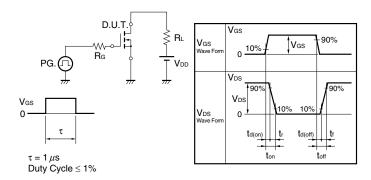
Note Pulsed

TEST CIRCUIT 1 AVALANCHE CAPABILITY

$V_{GS} = 20 \rightarrow 0 \text{ V}$ $PG. \bigcirc PG. \bigcirc PG.$



TEST CIRCUIT 2 SWITCHING TIME

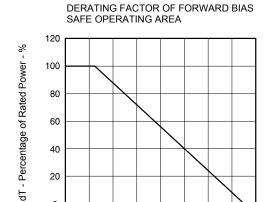


TEST CIRCUIT 3 GATE CHARGE

0

0 20 40

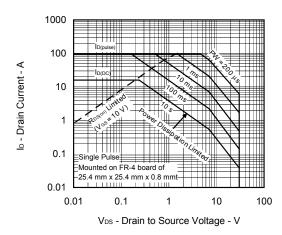
TYPICAL CHARACTERISTICS (TA = 25°C)



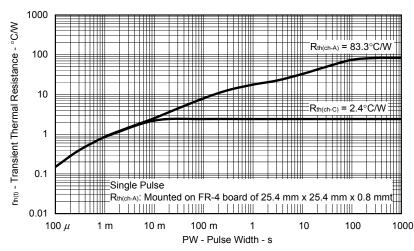
80 T_A - Ambient Temperature - °C

100 120 140 160

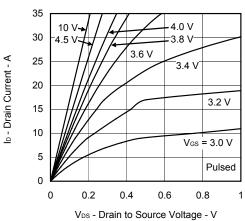
FORWARD BIAS SAFE OPERATING AREA



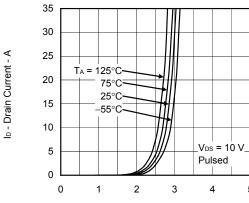
TRANSIENT THERMAL RESISTANCE vs. PULSE WIDTH



DRAIN CURRENT vs. DRAIN TO SOURCE VOLTAGE

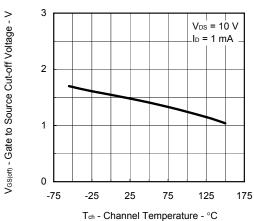


FORWARD TRANSFER CHARACTERISTICS

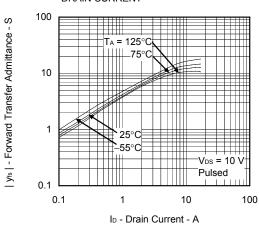


V_{GS} - Gate to Source Voltage - V

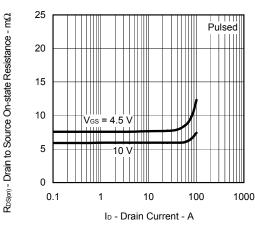
GATE TO SOURCE CUT-OFF VOLTAGE vs. CHANNEL TEMPERATURE



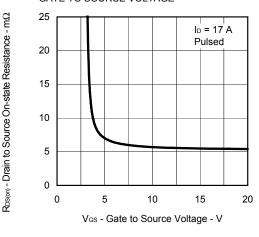
FORWARD TRANSFER ADMITTANCE vs. DRAIN CURRENT



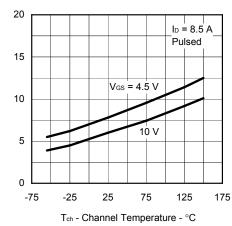
DRAIN TO SOURCE ON-STATE RESISTANCE vs. DRAIN CURRENT



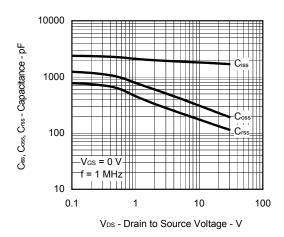
DRAIN TO SOURCE ON-STATE RESISTANCE vs. GATE TO SOURCE VOLTAGE



DRAIN TO SOURCE ON-STATE RESISTANCE vs. CHANNEL TEMPERATURE



CAPACITANCE vs. DRAIN TO SOURCE VOLTAGE



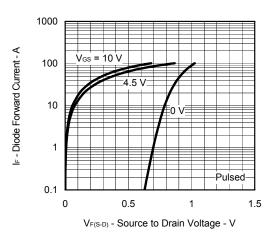
RDS(on) - Drain to Source On-state Resistance - m\Omega

NEC μ PA2800

DYNAMIC INPUT/OUTPUT CHARACTERISTICS

6 Vos - Gate to Source Voltage - V V_{DD} = 6 V 5 15 V 4 3 2 1 0 0 5 10 15 20 Q_G - Gate Charge - nC

SOURCE TO DRAIN DIODE FORWARD VOLTAGE



ORDERING INFORMATION

PART NUMBER	LEAD PLATING	PACKING	PACKAGE
μPA2800T1L-E1-AY Note			8-pin HVSON (3333)
μPA2800T1L-E2-AY Note	Pure Sn	Tape 3000 p/reel	0.028 g TYP.

Note Pb-free (This product does not contain Pb in the external electrode.)

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